

JMM6715N

Product Preview

60V N-Channel MOSFET



Features

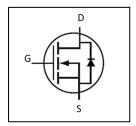
- Advanced shielded-gate technology
- Ultra-low on-resistance and gate-charge
- RoHS compliant

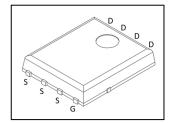
ROHS

Product Summary			
V _{DS} 60V			
	2.4 mΩ (Typ.)		
R _{DS} (ON)	2.9 mΩ (Max.)		

Applications

- Motor controllers
- DC-to-DC convertors
- Battery-driven electronic products, electrical equipment and machines





Ordering Information

Part Number	Marking	Package	Packaging
JMM6715N	MM6715N	DFN5x6	Tape & Reel



Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Drain-to-Source Voltage	V _{DS}	60	V
Gate-to-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, Silicon Limited (T _C = 25°C) (1)	I _D	125	
Continuous Drain Current, Silicon Limited (T _C = 100°C) (1)	I _D	79	
Continuous Drain Current, Silicon Limited t (T _A = 25°C) (2), (3)	ID	23	Α
Continuous Drain Current , Silicon Limited (T _A = 100°C) (2), (3)	ID	14	
Pulsed Drain Current (4)	I _{DM}	240	
Power Dissipation (T _C = 25°C)	P _D	86	W
Linear Derating Factor	-	0.69	W/°C
Single Pulse Avalanche Energy (5)	E _{AS}	130	mJ
Avalanche Current (6)	las	40	Α
Junction Temperature	Tı	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	

Thermal Characteristics

Parameter	Symbol	Max	Unit
Junction-to-Ambient Thermal Resistance (3)	R _{θJA}	45	°C/W
Junction-to-Case Thermal Resistance	R ₀ JC	1.45	C/W

Static Electrical Characteristics (7)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Drain-to-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V$, $I_D = 250 \mu A$	60	-	ı	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_{D} = 250 \mu A$	1.2	-	2.2	V
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V	-	-	1	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Drain to Course On Resistance	D	V _{GS} = 10V, I _D = 20A	-	2.4	2.9	~ 0
Drain-to-Source On-Resistance	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 20A	-	3.4	4.4	mΩ

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Dynamic Electrical Characteristics (7)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Forward Transconductance	g fs	V _{DS} = 5V, I _D = 30A	-	92	1	S
Total Gate Charge	Qg	V _{GS} = 10V,	-	54	-	
Gate-to-Source Charge	Qgs	V _{DS} = 30V,	-	8	-	nC
Gate-to-Drain Charge	Q _{gd}	I _D = 30A	-	12	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V,	-	23	-	
Rise Time	tr	V _{DS} = 30V,	-	62	-	
Turn-Off Delay Time	t _{d(off)}	I _D = 15A,	-	105	-	ns
Fall Time	t _f	$R_G = 3.0\Omega$	-	28	-	
Input Capacitance	Ciss	V _{GS} = 0V,	-	3467	-	
Output Capacitance	Coss	f = 1MHz,	-	1400	-	pF
Reverse Transfer Capacitance	Crss	V _{DS} = 25V	-	50	-	

Diode Characteristics (7)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 30A	-	0.8	-	V
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V$, $I_S = 30A$,	-	34	-	ns
Reverse Recovery Charge	Qrr	dls/dt = 100A/μs	-	50	-	nC

- (1) Rated according to $R_{\theta \text{JC}}$
- (2) Rated according to $R_{\theta JA}$
- (3) Surface–mounted on 1 inch² FR4 board, 2 oz Cu
- (4) Limited by maximum T_J
- (5) Starting T_J = 25°C, L = 0.1mH, V_{DD} = 30V, V_{GS} = 10V
- (6) Pulse width limited by maximum T_J
- (7) $T_J = 25$ °C unless otherwise specified



Typical Electrical Characteristics

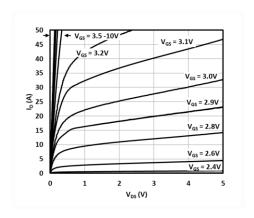


Fig. 1 Output characteristics

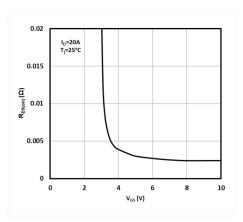


Fig.3 On-resistance vs. gate voltage

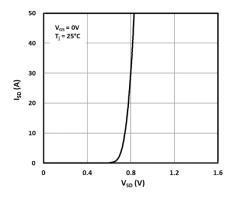


Fig.5 Source-to-drain diode forward characteristics

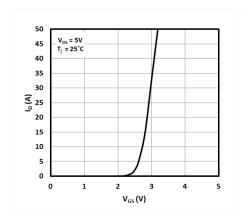


Fig. 2 Transfer characteristics

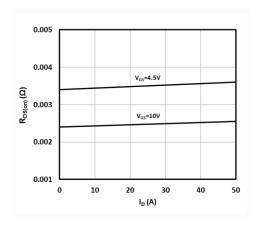


Fig.4 On-resistance vs. drain current

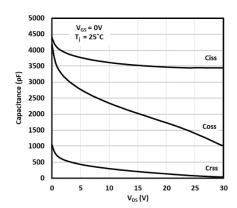
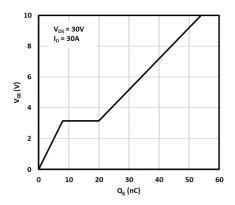


Fig.6 Capacitance vs. drain-to-source voltage





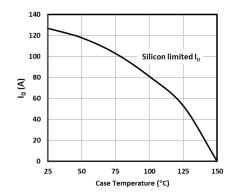


Fig.7 Gate-to-source voltage vs. gate charge

Fig.8 Maximum drain current vs. case temperature

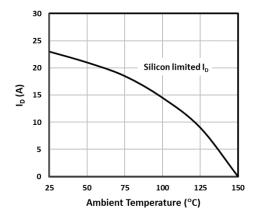
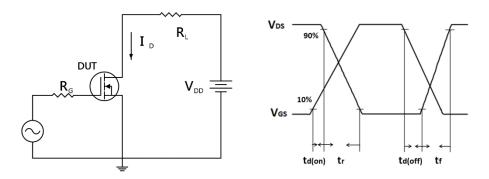


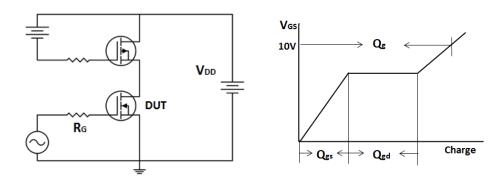
Fig. 9 Maximum drain current vs. ambient temperature



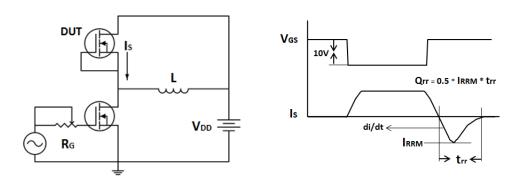
Test Circuits and Waveforms



Resistive switching time test circuit & waveforms

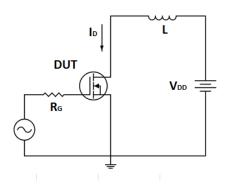


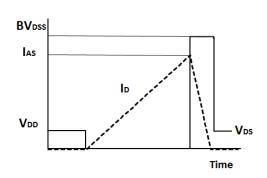
Gate charge test circuit & waveform



Peak diode recovery dv/dt test circuit & waveforms

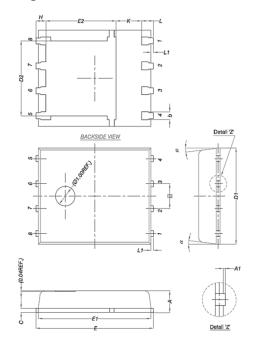






Unclamped inductive switching test circuit & waveforms

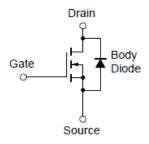
Package Drawing



	N	IILLIMETI	ERS
DIM.	MIN.	NOM.	MAX.
Α	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
С	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
Ε	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
е		1.27 BSC	
Н	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	<i>0</i> °	-	12°

DFN 5x6

Equivalent Circuit





Revision history of JMM6715N specification

Version	Change Items	Effective Date
1.00	Initial Release	26-Aug-20
1.01	Update drain current limits	14-Sep-20



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